NSN 5962-01-197-2166

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View Online at https://aerobasegroup.com/nsn/5962-01-197-2166

Body Length: 0.960 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** 0.185 inches **Maximum Power Dissipation Rating:** 200.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **Features Provided:** Monolithic and static operation and hermetically sealed **Inclosure Material:** Ceramic and glass **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Complementary-metal oxide-semiconductor logic **Input Circuit Pattern:** 15 input **Case Outline Source And Designator:** D-6 mil-m-38510 **Terminal Surface Treatment:**

Solder

Voltage Rating And Type Per Characteristic:

-0.3 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

120.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Rom

Memory Capacity:

Unknown

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

18 printed circuit

Specification Data:

81349-mil-m-38510/245 government specification

Shelf Life:

N/a

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Demilitarization:

Yes - demil/mli

Fiig:

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